arXiv:1303.7250v1 [cond-mat.mtrl-sci] 28 Mar 2013

Non-magnetic impurities to induce magnetism in α-PbO crystal structure

J. Berashevich and A. Reznik
Thunder Bay Regional Research Institute, 290 Munro St., Thunder Bay, ON, P7A 7T1, Canada and
Department of Physics, Lakehead University, 955 Oliver Road, Thunder Bay, ON, P7B 5E1

A new route to d^0 magnetism is established with help of the first principles methods. Non-magnetic interstitial impurities from group 14 in the periodic table are found to induce p-orbital magnetism in polycrystalline PbO-type structures. The half-filled p-orbitals occupied by two electrons is generated on the impurity site for which the ferromagnetic state of high stability is guaranteed by the first Hund's rule. Since the impurity is embedded between layers of the host, its atomic radius is a key to tune not only its solubility but also the magnetic behavior: the on-site stability of the spin polarized state grows with reduction of the atomic radius while losing in the long-rang order interactions. However, for impurities of smaller radius the weaker inter-site magnetic coupling can be compensated by their concentration as the impurity solubility limit is shifted to higher magnitudes.

The research on magnetic semiconductors has intensified in recent years due to requirements imposed by the rapidly developing field of spintronics [1]. Originally, magnetic semiconductors were created by doping conventional semiconductors with magnetic ions whose d or f orbitals are partially filled [2, 3]. The enormous attention given to the so-called "diluted magnetic semiconductors" has been rewarded with the discovery of a mechanism of the 'intrinsic' magnetism in semiconductors - defect-induced magnetism. Initially, in the semiconductors doped with magnetic ions, the intrinsic defects were considered only to mediate the magnetic coupling between localized spins occupying the partially filled d or f orbitals of ions thus contributing to the collective magnetism effect [4–6]. However, a better understanding of the defect properties has revealed that the defects generate sp localized spins able to generate the magnetic phenomenon [7–11]. The discovery of defect-induced magnetism dubbed as d^0 magnetism, i.e. magnetism which occurs not due to partially filled d orbitals of the magnetic ions, brought new impetus into field of magnetic semiconductors and more importantly in spintronics.

In order to pursue the spintronics application, the magnetic semiconductors are required to establish the magnetic percolation persisting at the room temperature. Such percolation is governed by interaction of the localized spins provided they show also the high on-site stability of the spin-polarized state. In practice to induce d^0 magnetism, the weaker are interactions between the localized spins, the higher concentration of the defects carrying the localized spins has to be adapted [7, 8]. However, raising a defect concentration is not always a straightforward solution [3]. For those defects known to induce magnetism: the vacancy [10–12] and substitutional defects [13–15], the low limit to the defect concentration even at the most favorable growth conditions is applied because of their rather high formation energy [12]. Moreover, defects especially in high concentration are not always mechanically tolerated by the crystal lattice of the host, not to mention that the defect-induced lattice perturbation may lead to unwanted changes in the electronic properties [3]. Therefore, although an idea of intrinsic magnetism in semiconductors is attractive, it requires some efforts to bring it to the level of practical applications.

In this respect, our recent finding of new route to d^0 magnetism offers an elegant solution and promises a breakthrough in development of magnetic semiconductor [16]. We found that the Pb interstitial defects in α-PbO are capable to induce d^0 magnetism [16]. The origin of magnetism upon bonding of the impurity with the host, is unique; the Pb interstitial of Pb_i:$6s^2 6p^2$ outer shell utilizes its only Pb_i:$6s^2$ electrons to connect to the host while leaving on site two unpaired $6p^2$ electrons. The Hund's rule dictates the spin alignment of the $6p^2$ electrons which manifests in on-site magnetic moment of 2.0 μB and the high stability of the spin polarized state defined by difference in total energy of the anti- and ferromagnetic states (AFM and FM) as $E_{\mathrm{M}} = E_{\mathrm{AFM}} - E_{\mathrm{FM}}$=0.235 eV [16]). Thus, the Pb atom being nonmagnetic in nature gains magnetization upon embedding as the interstitial defect into the α-PbO crystal lattice. In analogy with magnetic ions, magnetism occurs due to partially filled orbitals, but with one substantial difference, here it is due to the p orbital.

In terms of large lattice distortion generated by the defects in crystalline materials (only crystalline systems have been considered in all previous studies devoted to d^0 magnetism [10–15]), the layered type of the crystal structure of α-PbO helps to avoid this issue. The interstitial defects in the α-PbO lattice are accommodated within the interlayer space or on the surface of crystallites thereby minimizing the negative impact of defects on the crystal lattice of the host. It results in lowering of the formation energy of defects and promises a better mechanical tolerance of the host lattice to such defects. Moreover, the mechanism of bonding of the interstitial to the host is unique itself because only the s^2 valence electrons from both the host and the defect sides are involved in the bonding. In particular, the Pb_i:$6s^2$ outer shell electrons of the interstitial through excitation to the Pb_i:$6s^1p^1$ state participate in the bond formation with the host Pb:$6s^2$ electrons [16]. Since in the band diagram of the host [17] the bands near the gap edges are

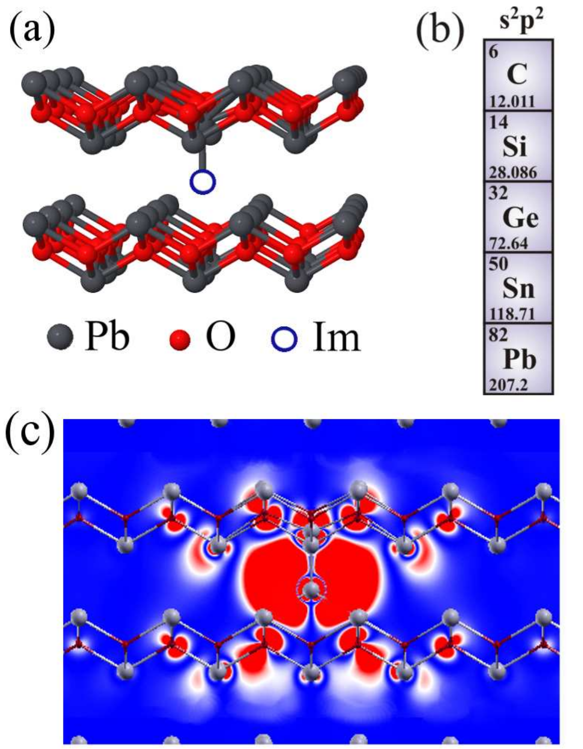

FIG. 1: (a) The α-PbO crystal structure which contains the impurity interstitial atom. (b) The list of impurities used to generate magnetism (the atomic number on the top and the standard atomic weight at the bottom). (c) The Pb self-interstitial: the spin density map is plotted with isovalues of ± 0.003 e/Å^3 in Xcrysden for the energy range $(E_D + E_V) \pm 0.15$ eV. It demonstrates formation of the FM state at the impurity site for which defect tails can be traced up to the last oxygen atom shown.

formed mainly by the host Pb:6p and the O:2p electrons, but doping involves only the s electrons it is almost non-invasive to the host band behavior other than appearance of the defect-induced bands. Therefore, taking all these into account, a lattice of the α-PbO-type is expected to tolerate the high concentration of Pb interstitials to be limited only by thermodynamics of the defect formation.

Synopsis on the origin of the p-orbital magnetism in the α-PbO crystal lattice: the lone pair of s^2 outer shell electrons from the host and the s^2p^2 outer shell from the impurity are required. Because the presence of s^2 outer shell electrons is a typical feature of α-PbO lattice, 'other' compounds of this type can be used as the host lattice. In fact, α-PbO crystal structure is well recognized in superconductivity [18]: Fe-pnistides (basics are FeSe, FeAs), cuprate (basics are CuO, CuS), and lanthanum compounds (basics are LaF, LaO). However, since for the defect-induced magnetism the wide gap semiconductor is preferable, the α-PbO compound is seems to be the best candidate anyway. In regards to impurity choice, the similar statement is applied; instead of Pb atom 'other' chemical elements possessing the s^2p^2 outer shell configuration can be used as the magnetic impurity. The selection of impurity can be even further extended to the chemical elements of the s^2p^3 outer shell which were found to build the on-site magnetic moment of 1.0 μB [16]. However, closer look to s^2p^3 systems has revealed the weak spin-polarization of the p^3 localized state (for the Sb impurity, the spin polarization energy is only 0.046 eV) that implies the low temperature limit on an appearance of magnetism making it less suitable for device applications. Therefore, in this work we consider the chemical elements of the s^2p^2 configuration, i.e. from group 14th in the periodic table (see the list of elements in Fig. 1(b)), as potential candidates to induce d^0 magnetism in the α-PbO crystal lattice. Because we expect a difference in the atomic radius of these elements influencing their magnetic behavior, the possibility to tune magnetism is investigated here. If our hypothesis is proven true, this approach can open a wide perspective to design the desired magnetic strength in the α-PbO magnetic semiconductor.

In our study we applied the generalized gradient approximation (GGA) with the PBE parametrization [19] provided by WIEN2k package for the density functional calculations [20] (augmented plane wave + local orbitals approach). The Pb:5p, 5d, 6s, 6p and O:2s, 2p electrons have been treated as the valence electrons. The supercell approach (RKmax=7) with sufficiently large supercell of 108-atom size (3×3×3 array of the primitive unit cells) has been used for single impurity calculation while the 190-atom size (4×4×3) supercell for the interacting defects. For integration of the Brillouin-zone, the Monkhorst-Pack scheme of the 5×5×4 (or 4×4×2) k-mesh was applied. The formation energies of the interstitial defects to be considered here for the vacuum conditions have been calculated with help of formalism described elsewhere [21]. Because the distance between layers in the α-PbO structure defined by the lattice constant c_0 contributes into the formation energy, the experimental value of c_0=5.07Å [22] has been used for those calculations, while the band structure properties have been evaluated with the optimized lattice parameters as described in [21].

Our previous study [16] has revealed that magnetism originated from the p-type localized spins of the Pb interstitial seems to combine advantages of the vacancy induced d^0 magnetism [7–11] and magnetism due to the magnetic ions [2, 3]. Because spin ordering of $6p^2_{x+y}$ electrons on site of the Pb interstitial is governed by the Hund's rule, it therefore causes the high on-site stability of the ferromagnetic state. At the same time, hybridization of impurity state with the host lattice results in the extended defect tails promising to induce the long-range order interactions. As shown in Fig. 1(c), the defect tails appear in upper and lower layers, they are extended up to seven nearest-neighbors and show the higher spin localization at the oxygen atoms. Although the impurity interacts with the top layer through bonding while with bottom layer only through the hybridization interactions,

TABLE I: The stability of the spin-polarized state as a function of impurity atomic radius R_{Im} [24]: the spin-polarization energy $E_{\mathrm{M}} = E_{\mathrm{AFM}} - E_{\mathrm{FM}}$ and the energy splitting of the 1^u and 1^d bands $(E_1 - E_2)$. Im-Pb is the double bond length.

Im	R_{Im}, Å	Im-Pb, Å	E_{M}, eV	$(E_1 - E_2)$, eV
Pb	1.81	2.90	0.235	0.523
Sn	1.72	2.86	0.258	0.585
Ge	1.52	2.70	0.306	0.680
Si	1.46	2.65	0.338	0.734
C	0.90	2.30	0.538	1.058

the defect tail are observed to be more pronounced at the bottom layer. It occurs because the Pb interstitial is tightly sandwiched between layers that results in its strong hybridization with the bottom layer. The redistribution of the spin density from defect site to the host lattice is probably reason of the on-site stability of the ferromagnetic state found for the Pb interstitial (E_{M}=0.235 eV) to be at least twice lower than that known for the magnetic impurity of d or f types [23]. It is natural to assume that for impurity with smaller atomic radius the hybridization with the bottom layer will be suppressed that should result in enhancement of on-site stability of the localized spins. Our study on magnetic behavior of the chemical elements from the group 14th embedded as the interstitial defects into the α-PbO crystal structure supports this hypothesis. We have considered an alteration in the band behavior as shown in Fig. 2, while the energetic (spin-polarization energy) and structural parameters are disclosed in Table I.

In the band diagram (see Fig. 2 (a)), there are several bands associated with impurity, 1^u and 1^d are those induced by p-localized electrons (the spin-up band 1^u is occupied by two electrons, while spin-down band 1^d is empty) while the 2^u and 2^d bands forming the top of the conduction band (E_C) both appear due to the antibonding orbitals of the impurity-host bond (Im-Pb). It was found that reduction in atomic radius of dopant leads to shift of both impurity bands 1^u and 1^d (1^u is occupied by two electrons, while 1^d is empty) towards the valence band (E_V) but in the same time the gradual enhancement of the energy splitting of these bands occurs. The 2^u band is also shifted towards the lower energy due to shortening of the Im-Pb bond, while the energetic position of the 2^d band deviates in narrow energy range near $\sim$ 1.8 eV. The enhanced splitting of the 1^u and 1^d bands (see $(E_1 - E_2)$ in Table I) indicates a gain in stability of the spin-polarized state and, indeed, a raise in the spin-polarization energy E_{M} is observed. We found that for the Si and C impurities the on-site stability already approaches the values known for the magnetic ions of d or f types [23].

In accordance with our expectation, a rise in on-site spin stability with reduction of the atomic radius of impurity is obtained. Moreover, the impurity of smaller radius was found to induce less distortion into the α-PbO crystal structure: in order to accommodate the Pb interstitial the layers of the host move apart while for impurity of smaller radius the interlayer distance is preserved. As a result, reduction in atomic radius of the interstitial atom results in suppression of the formation energy of defect: 1.23 eV is found for Pb interstitial, 0.79 eV for the Sn interstitial, just above zero for Ge and Si, and it is becoming negative for C interstitial. The low formation energy promises not only the better mechanical tolerance of the lattice to defects but also the higher finite defect concentration to be reached: thermodynamically granted defect concentration for the negative formation energy can be as high as number of the sites available for bonding $\sim 10^{22}$ cm^{-3}. Therefore, the C interstitial shows the most encouraging magnetic behavior so far: the highest on-site

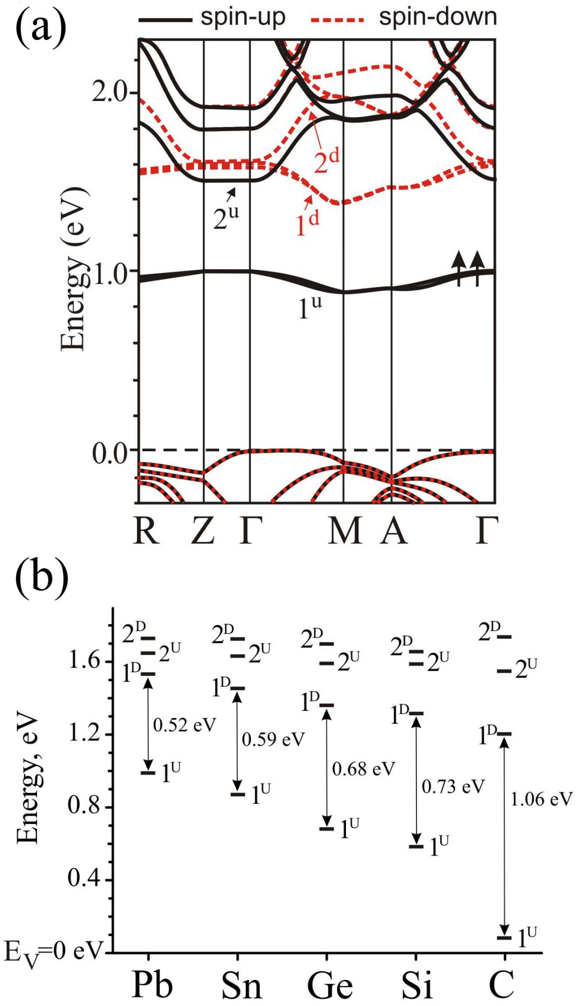

FIG. 2: (a) The band diagram for the α-PbO crystal structure containing the Pb self-interstitial defect: 1^u and 1^d are the bands formed by the p-localized electrons Pb:$6p^2_{x+y}$ while 2^u and 2^d are the antibonding orbitals of the Im-Pb bond [16]. (b) The energetic location of the 1^u, 1^d, 2^u and 2^d bands relative the top of the valence band E_V for the different impurities.

stability (E_M=0.538 eV) and the negative formation energy. Unfortunately, the high on-site stability suggests the stronger localization of the spin density at the defect site that might affect the long-order interactions.

The collective magnetic ordering can only occur when two impurities are close enough to each other to establish the magnetic coupling of their localized spins and in this respect the long range order interactions play the crucial role. The magnetic coupling between impurities has been simulated for the system containing two interstitials of the same type placed on distance of ∼4 Å within the 3×3×3 supercell. The p^2_{x+y} electrons localized on impurities have been aligned on-site, while their inter-impurity ordering has been switched from antiferromagnetic to ferromagnetic in order to evaluate $E_\mathrm{M} = E_\mathrm{AFM} - E_\mathrm{FM}$. The $6p^2_{x+y}$ state is exactly half filled and, therefore, for two interacting impurities when their localized electrons are ferromagnetically coupled (in this particular case all four localized spins in the system are aligned and the magnetic moments is 4 μ_b), the inter-site virtual hopping is not allowed [3, 10]. In case of AFM coupling, the virtual hopping is allowed leading to lowering of the total energy of the system such as the AFM state becomes the ground state. For two Pb interstitials placed on distance ∼4 Å we found that $E_\mathrm{M(Pb\text{-}Pb)}$=-0.96 eV (a negative sign indicates the AFM ground state) while for the case of two interacting C interstitials it is only $E_\mathrm{M(C\text{-}C)}$=-0.38 eV. The electronic interactions and so the magnetic coupling between defects exponentially drop down as the distance between them increases. Thus, for two defects separated by a distance 11.5 Å (for this calculation the size of the supercell was 4×4×3), the energy difference between AFM and FM states is drastically supressed to $E_\mathrm{M(Pb\text{-}Pb)}$=-0.0056 eV and $E_\mathrm{M(C\text{-}C)}$=-0.0023 eV for the Pb and C interstitials, respectively. Therefore, we found that the larger is the atomic radius of impurity, the stronger is the hybridization of the impurity state with the host lattice that results in extended defect tails being an essential to establish the long-range order interactions. For the magnetic percolation to be reached, a reduction in inter-impurity coupling to occur for the impurities of smaller atomic radius can be compensated by their concentration as the thermodynamic limit to the defect concentration is lifted to the higher magnitudes.

In summary, we propose to generate d^0 magnetism in compounds of α-PbO crystal structure by doping with non-magnetic impurities belonging to group 14th of the periodic table. In analogy with magnetic ions, origin of magnetism is due to partially filled orbitals, but instead of d or f types it is being of p-type in this case. The partial occupation of p orbital appears as a result of the unique bonding of non-magnetic impurities of s^2p^2 outer shell with the host lattice: two p^2_{x+y} electrons are left on-site of impurity after bonding and the first Hund's rule dictates their ferromagnetic ordering. We found that the magnetic behavior of the dopants depends on their atomic radius: dopant with the smaller radius establishes the higher on-site stability of the localized spin. For the Si and C impurities, the on-site stability reaches such a high magnitude that it becomes comparable with that for the magnetic ions of d or f types [23]. Another benefit of the small atomic radius of impurity is its near zero defect formation energy that shifts the solubility limit to magnitudes as high as $\sim 10^{22}$ cm^{-3}. However, in terms of the collective magnetic ordering to occur, the trade-off between the on-site stability and the long-range order interactions has to be made: the stronger on-site stability implies the weaker long-range order interactions. Therefore, to establish the magnetic percolation with non-magnetic impurities from 14th group of the periodic table, one rule should be followed: the smaller the atomic radius of element the weaker magnetic coupling between impurities would occur to be compensated by higher doping concentration.

I. ACKNOWLEDGEMENT

This work was made possible by the computational facilities of Dr. O. Rubel and the Shared Hierarchical Academic Research Computing Network (SHARCNET:www.sharcnet.ca) and Compute/Calcul Canada. Financial support of Ontario Ministry of Research and Innovation through a Research Excellence Program Ontario network for advanced medical imaging detectors is highly acknowledged.

---

[1] K. Ando, Science 312, 1883 (2006).
[2] P. Mahadevan, A. Zunger, D.D. Sarma, Phys. Rev. Lett. 93, 177201 (2004).
[3] A. Zunger, S. Lany, H. Raebiger, Physics 3, 53 (2010)
[4] H.J. Hu et al., J. Phys.: Condens. Matter 22, 016002 (2010).
[5] T. Dietl, H. Ohno, F. Matsukura, J. Cibert, D. Ferrand, Science, 287, 1019 (2000).
[6] Y. Gohda, A. Oshiyama, Phys. Rev. B 78, 161201 (2008).
[7] J.M.D. Coey, Solid State Sciences 7, 660 (2005).
[8] M. Venkatesan, C.B. Fitzgerald, and J.M.D. Coey, Nature 430, 630 (2004).
[9] R. Podila et al., Nano Letters 10, 1383 (2010).
[10] P. Dev, Y. Xue, and P. Zhang, Phys. Rev. Lett. 100, 117204 (2008).
[11] H. Peng et al., Phys. Rev. Lett. 102, 017201 (2009).
[12] J. Osorio-Guillen, S. Lany, S.V. Barabash, A. Zunger, PRL 96, 107203 (2006)
[13] Z. A. Khan, S. Ghosh, Appl. Phys. Lett. 99, 042504 (2011).
[14] L.-H. Ye, A. J. Freeman, and B. Delley, Phys. Rev. B 73, 033203 (2006).

[15] L. Shen, et al., Phys. Rev. B 78, 073306 (2008).
[16] J. Berashevich, A. Reznik, submitted to the journal.
[17] J. Berashevich, O. Semeniuk, J.A. Rowlands, A. Reznik, EPL 99, 47005 (2012).
[18] P. A. Lee, N. Nagaosa, X.-G. Wen, Rev. Mod. Phys. 17, 78 (2006).
[19] J.P. Perdew, K. Burke, and M. Ernzerhof, Phys. Rev. Lett. 77, 3865 (1996).
[20] P. Blaha, K. Schwarz, G. K. H. Madsen, D. Kvasnicka, and J. Luitz, Wien2k: An Augmented Plane Wave + Local Orbitals Program for Calculating Crystal Properties: Karlheinz Schwarz, (Techn. Universitat Wien, Austria, 2001)
[21] J. Berashevich, O. Semeniuk, O. Rubel, J.A. Rowlands, and A. Reznik, J. Phys.: Condens. Matter. 25, 075803 (2013).
[22] S. Venkataraj, J. Geurts, H. Weis, O. Kappertz, W.K. Njoroge, R. Jayavel, M. Wuttig, J. Vac. Sci. Technol. A 19, 2870 (2001).
[23] J. F. Janak, Phys. Rev. B 16, 255 (1977).
[24] J. C. Slater, Journal of Chemical Physics 41, 3199 (1964).